TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))						Docket No. SETI-0002DIV		
	In Re Application Of:  Khan et al.							
	Serial No. Filing Date 10/647,714  Filing Date 8/25/2003  Examiner Unknown  Unknown  Unknown							
Title: N	Title: METAL OXIDE SEMICONDUCTOR HETEROSTRUCTURE FIELD EFFECT TRANSISTOR							
			Address to:					
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			37 CFR 1.97(b)					
	The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.							
	37 CFR 1.97(c)							
	2. The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:							
☐ the statement specified in 37 CFR 1.97(e);								
OR								
☐ the fee set forth in 37 CFR 1.17(p).								

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"Optoelectronic GaN-based Field Effect Transistors," M. S. Shur et al., SPIE, Vol. 2397, pp. 294-303, Feb. 7, 1995.								Seb. 7, 1995.		
"High Pinch-off Voltage AlGaN-GaN Heterostructure Field Effect Transistor." M. S. Shur et al., Proceedings of ISDRS	· · · · · · · · · · · · · · · · · · ·		"High Pinch-off Voltage	ge AlGaN-GaN Hete	rostructure Field Effect Transis	tor," M. S. Shu	ır et al., Proce	edings of ISDRS-	97.	
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		No. 141: Chapter 4, Pres	sented at Int. Symp	Characteristics of GaN FET Stru Compound Semicond., San Die	ego, CA, Sept. 1	8-22, 1994, pp	. 459-462.	
		"GaN - AlxGa1-xN Hete Insulator Semiconductor	erostructures Depos r Field Effect Trans	sition by Low Pressure Metalor sistor (MISFET) Devices," M. K	ganic Chemical Chan et al Mat	Vapor Deposi erial Research	tion For Metal Society Symposium	
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·		Filing Date 9/27/2001	Group Art Unit 2818
*EXAMINER	OTHER DOCUMENTS (Including Author,	r, Title, Date, Pertinent Pages, Etc.)	
PE 3 7003	Ren, F. et al., "Effect f temperature on Ga2O3 Physics Letters, Vol. 73, No. 26, 28 December 19	(Gd2O3)/GaN metal-oxide-semicond 998, pp. 3893-3895.	uctor field-effect transistors," Applied
WIN O 3 TRADENTAL	Gaska, R. et al., "Electron mobility in modulation 2, 11 January 1999, pp. 287-289.	on-doped AlGaN-GaN heterostructur	res," Applied Physics Letters, Vol. 74, No.
	Khan, M.A. et al., "Current/voltage characteris transistors at high drain bias," Electronics Lette	stic collapse in AlGaN/GaN heterostri ters, Vol. 30, No. 25, 8 December 1994	ucture insulated gate field effect I, pp. 2175-2176.
	Carrano, J.C. et al., "Very low dark current me GaN epitaxial layers," Applied Physics Letters,	etal-semiconductor-metal ultraviolet j , Vol. 70, No. 15, 14 April 1997, pp. 19	photodetectors fabricated on single-crystal 992-1994.
	Chen, Q. et al., "Schottky barrier detectors on (No. 17, 28 April 1997, pp. 2277-2279.	GaN for visible-blind ultraviolet detec	ction," Applied Physics Letters, Vol. 70,
	Khan, M.A. et al., "AlGaN/GaN metal-oxide-ser Applied Physics Letters, Vol. 77, No. 9, 28 Augu	miconductor heterostructure field-eff ust 2000, pp. 1339-1341.	ect transistors on SiC substrates,"
	Shur, M.S. and Khan, M.A., "GaN and AlGaN I Science Publishers, Series Optoelectronic Proper II, pp. 47-92, S. Pearton, Editor (1999).	Devices: Field Effect Transistors and erties of Semiconductors and Superlat	Photodetectors," Gordon and Breach tices, Vol. 7 GaN and Related Materials
	Shur, M.S. and Khan, M.A., "Wide Band Gap S 23rd Int. Symp. Compound Semiconductors, St.	Semiconductors. Good Results and G. Petersburg, Russia, 23-27 September	reat Expectations," Paper presented at r 1996, pp. 25-31.
	Khan, M.A. et al., "AlGaN/GaN Metal Oxide Se Letters, Vol. 21, No. 2, February 2000, pp. 63-65	emiconductor Heterostructure Field 15.	Effect Transistor," IEEE Electron Device
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